

### Abstract of the Disclosure

An infrared photodetector for high absorption efficiency at room or near room  
5 temperature is disclosed. The invention teaches a special design of quantum wells to  
obtain the desired performance. A quantum well infrared photodetector having a multi-  
quantum well structure for providing high absorption at room temperature and providing  
substantial dark current at room temperature is disclosed. The device also has contacts for  
receiving current from the multi-quantum well structure.

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